

**ISP817X, ISP827X, ISP847X
ISP817, ISP827, ISP847**



ISOCOM
COMPONENTS

**HIGH DENSITY MOUNTING
PHOTOTRANZISTOR
OPTICALLY COUPLED ISOLATORS**



APPROVALS

- UL recognised, File No. E91231 under Package System 'EE'

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form : -
 - STD
 - G form
 - SMD approved to CECC 00802

DESCRIPTION

The ISP817, ISP827, ISP847 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages.

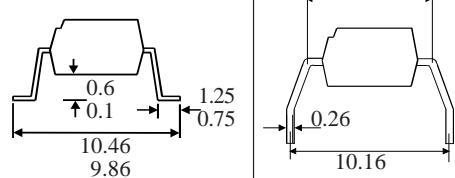
FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Current Transfer Ratio (50% min)
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High BV_{CEO} (35Vmin)
- All electrical parameters 100% tested
- Custom electrical selections available

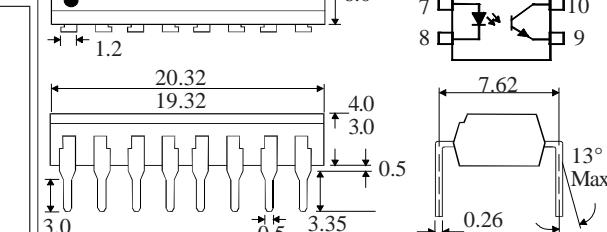
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

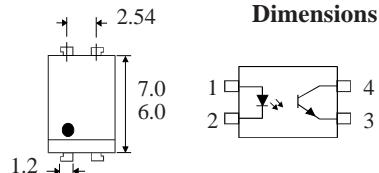
**OPTION SM
SURFACE MOUNT**



OPTION G

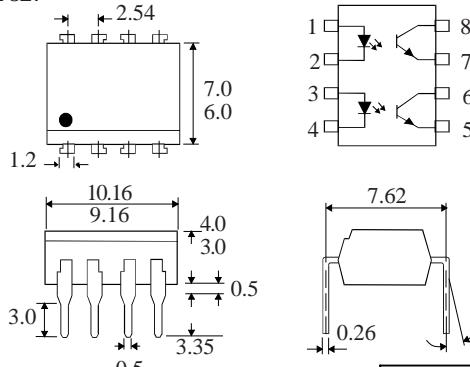


**ISP817X
ISP817**

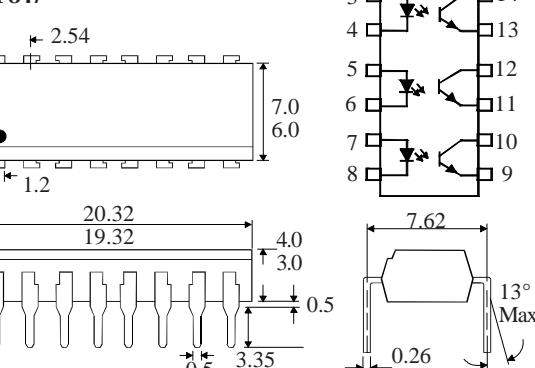


Dimensions in mm

**ISP827X
ISP827**



**ISP847X
ISP847**



ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	—	-55°C to + 125°C
Operating Temperature	—	-30°C to + 100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)		260°C

INPUT DIODE

Forward Current	—	50mA
Reverse Voltage	—	6V
Power Dissipation	—	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV _{CEO}	—	35V
Emitter-collector Voltage BV _{ECO}	—	6V
Collector Current	—	50mA
Power Dissipation	—	150mW

POWER DISSIPATION

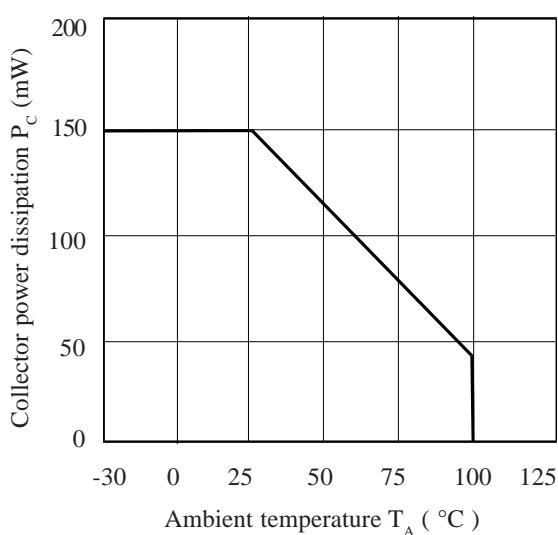
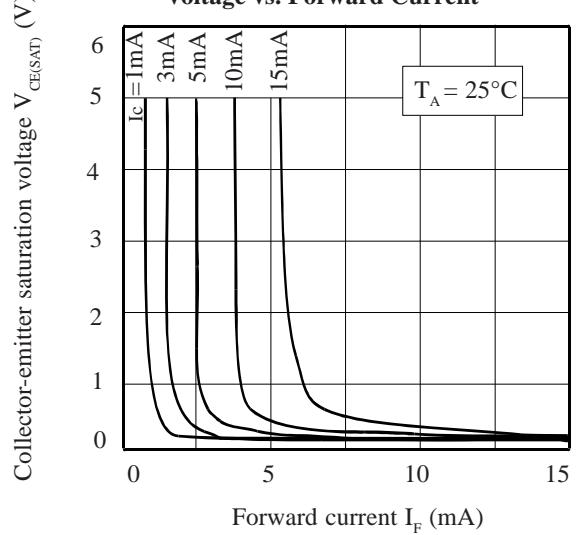
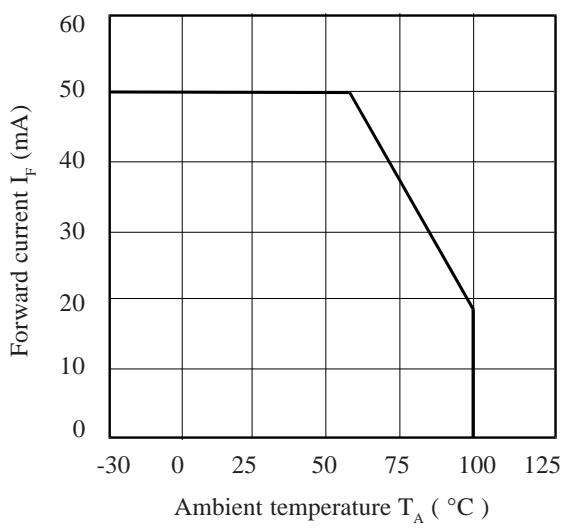
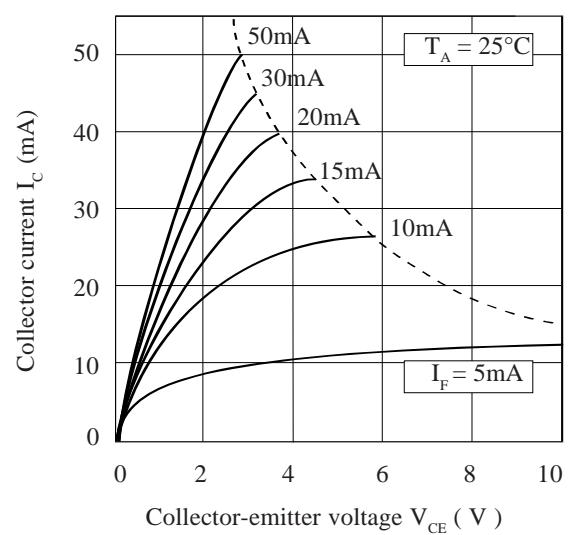
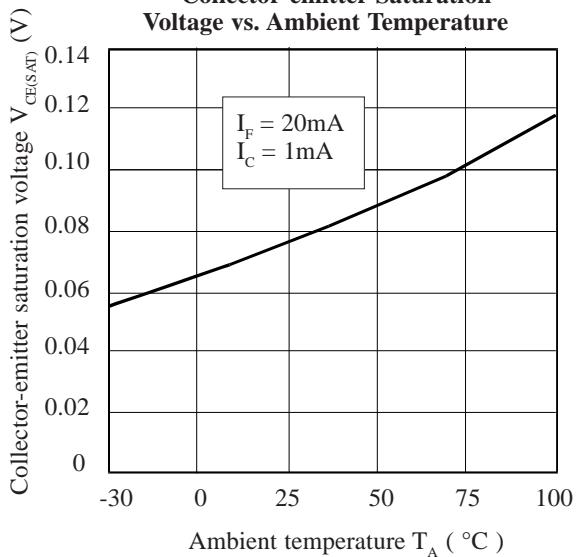
Total Power Dissipation	—	200mW
(derate linearly 2.67mW/°C above 25°C)		

ELECTRICAL CHARACTERISTICS (T_A = 25°C Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V _F)		1.2	1.4	V	I _F = 20mA
	Reverse Current (I _R)			10	µA	V _R = 4V
Output	Collector-emitter Breakdown (BV _{CEO})	35			V	I _C = 1mA
	Emitter-collector Breakdown (BV _{ECO})	6			V	I _E = 100µA
Coupled	Collector-emitter Dark Current (I _{CEO})			100	nA	V _{CE} = 20V
	Current Transfer Ratio (CTR) (Note 2) ISP817, ISP827, ISP847	50		600	%	5mA I _F , 5V V _{CE}
	GB	100		600	%	5mA I _F , 5V V _{CE}
	BL	200		600	%	5mA I _F , 5V V _{CE}
	A	80		160	%	5mA I _F , 5V V _{CE}
	B	130		260	%	5mA I _F , 5V V _{CE}
	C	200		400	%	5mA I _F , 5V V _{CE}
	D	300		600	%	5mA I _F , 5V V _{CE}
	Collector-emitter Saturation Voltage V _{CE(SAT)}			0.2	V	20mA I _F , 1mA I _C
	Input to Output Isolation Voltage V _{ISO}	5300			V _{RMS}	See note 1
		7500			V _{PK}	See note 1
	Input-output Isolation Resistance R _{ISO}	5x10 ¹⁰			Ω	V _{IO} = 500V (note 1)
	Output Rise Time tr		4	18	µs	V _{CE} = 2V ,
	Output Fall Time tf		3	18	µs	I _C = 2mA, R _L = 100Ω

Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

Collector Power Dissipation vs. Ambient Temperature**Collector-emitter Saturation Voltage vs. Forward Current****Forward Current vs. Ambient Temperature****Collector Current vs. Collector-emitter Voltage****Collector-emitter Saturation Voltage vs. Ambient Temperature****Current Transfer Ratio vs. Forward Current**